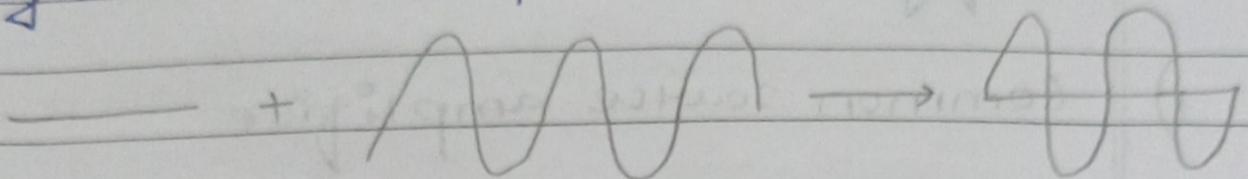


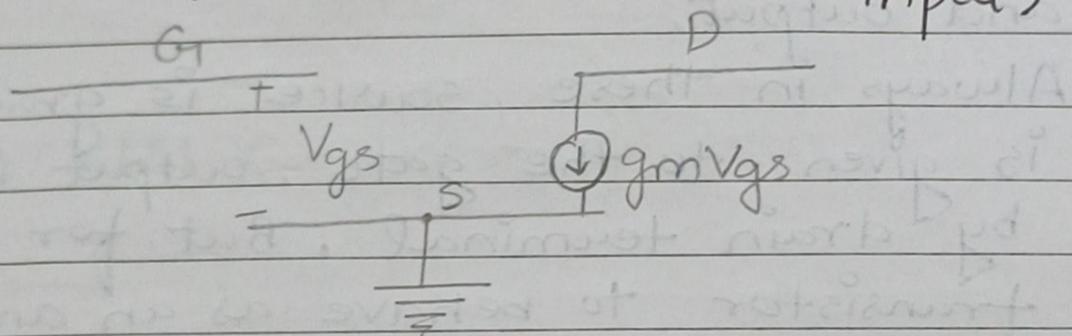
Unit-3-MOSFET as an Amplifier

; Small signal equivalent circuit

An amplifier will have AC signal as the input (because it has to amplify) and a DC voltage is there to bias the transistor to push it into saturation region. The output is AC-DC mixed.



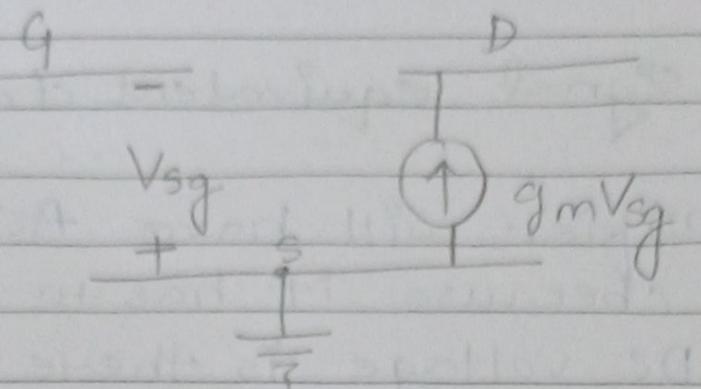
Small signal model for NMOS (AC signal input)



Gate and source have no physical connection they are connected by gate voltage V_{gs} (small letter - g and s as input is ac signal). We apply the gate voltage for NMOS so gate is +ve and s is -ve. When V_{gs} is applied, drain current flows from D to S. $I_d = gmV_{gs}$. We prefer writing gmV_{gs} rather than I_d as it is voltage controlled current device.

PMOS: (Invert Logic Using PMOS)

In channel length modulation there is a resistance r_o between D and S.

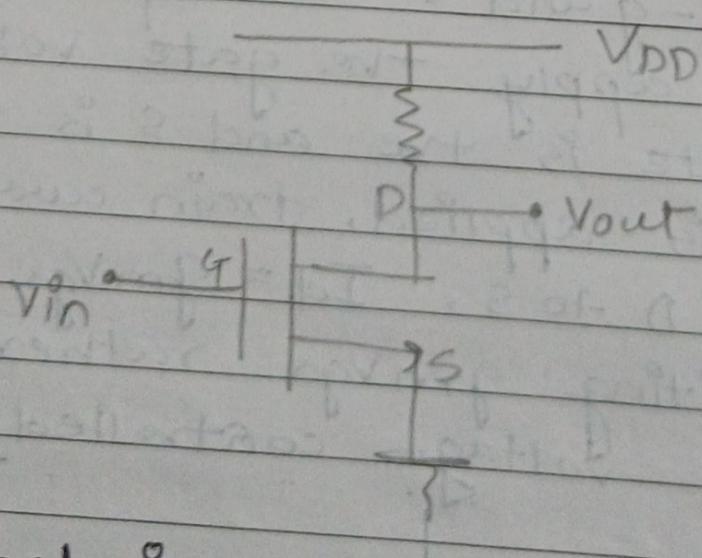


: Configuration

1) Common source amplifier

When small signal model is drawn, source terminal is common to input and output.

Always in these, source is grounded, input is given to the gate, output is given by drain terminal. But for the transistor to behave as an amplifier, it must be in SR. But V_{dd} cannot be applied directly to drain as then $V_{out} = V_{DD}$. That's why load resistance is used.

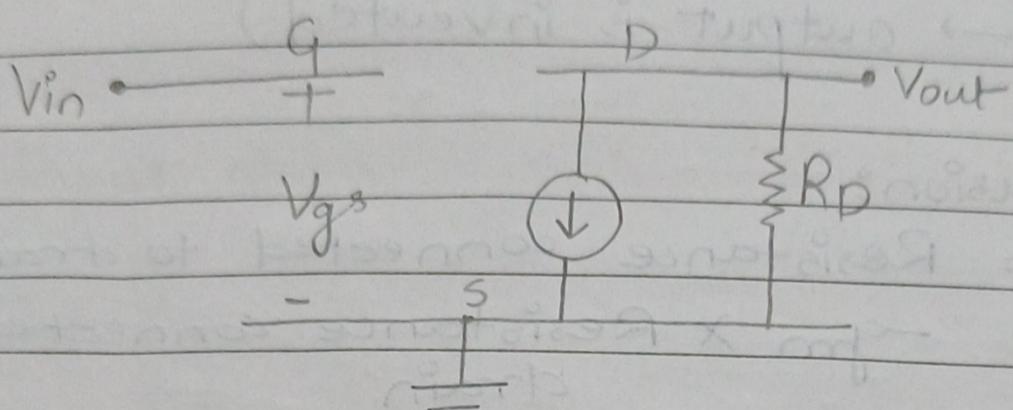


Analysis:

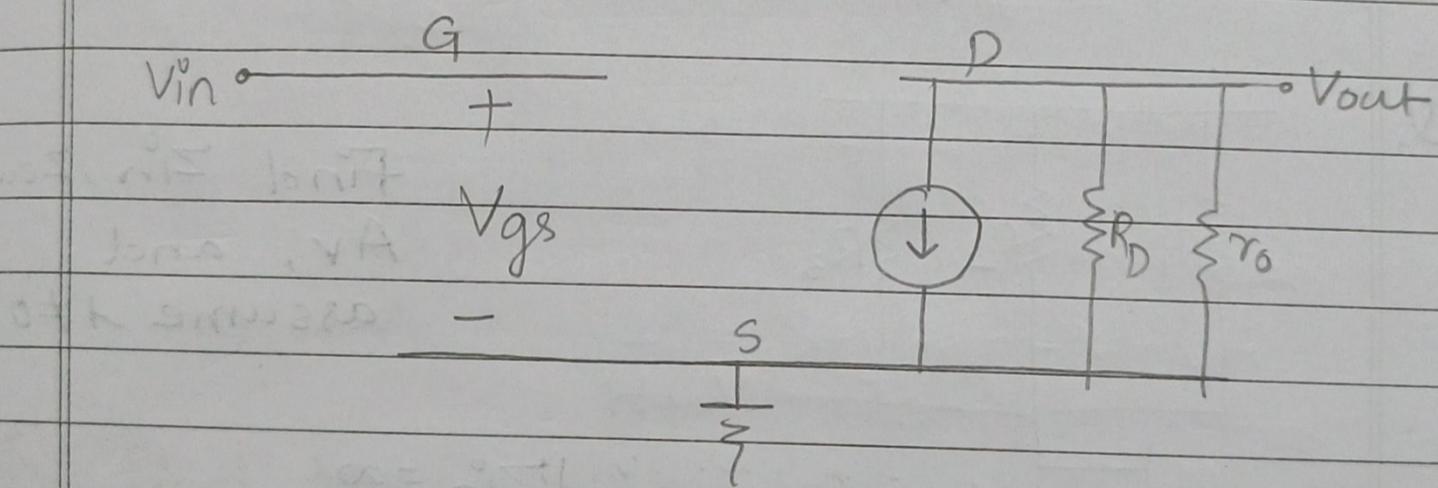
(Drawing small signal model)

Analysing the transistor only when AC is applied without DC voltage (biasing) is called small signal model. (All DC voltages are shorted and DC currents are open circuited)

Without CLM ($C_1 = 0$)



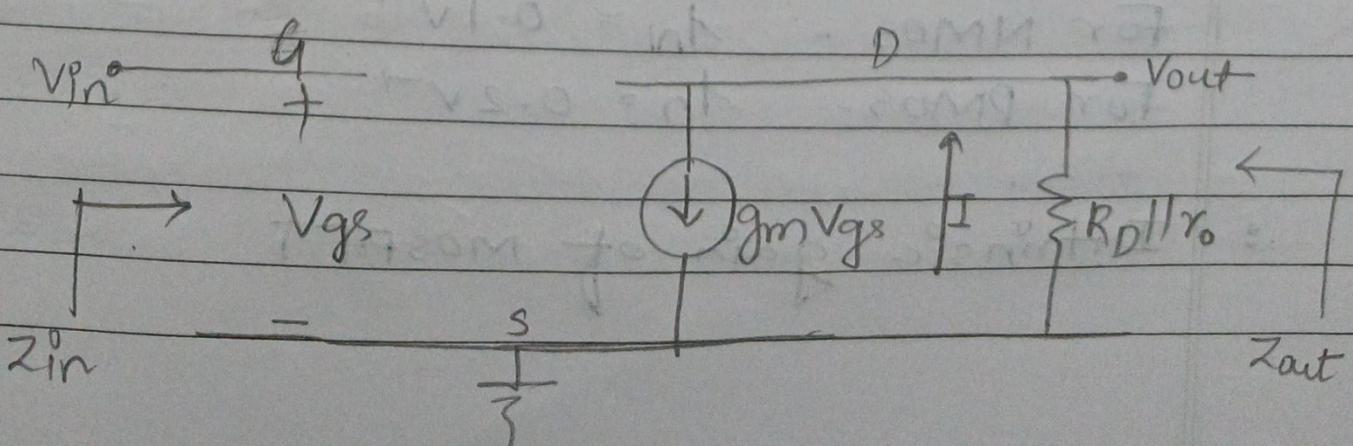
With CLM ($C_1 \neq 0$)



$$r_o = \frac{V_A}{I_D} = \frac{-1}{A I_D}$$

$$\text{If } C_1 = 0 \quad r_o = \infty$$

$$R_D \parallel r_o = R_D$$



CS amplifier: Phase reversal

$$Z_{in}^o = \infty$$

$$Z_{out} = R_D \parallel r_o$$

$$A_v = \frac{V_{out}}{V_{in}} = -g_m \frac{V_{gs}}{V_{ds}} (R_D \parallel r_o)$$

$$A_v = -g_m (R_D \parallel r_o)$$

(-ve \rightarrow output is inverted)

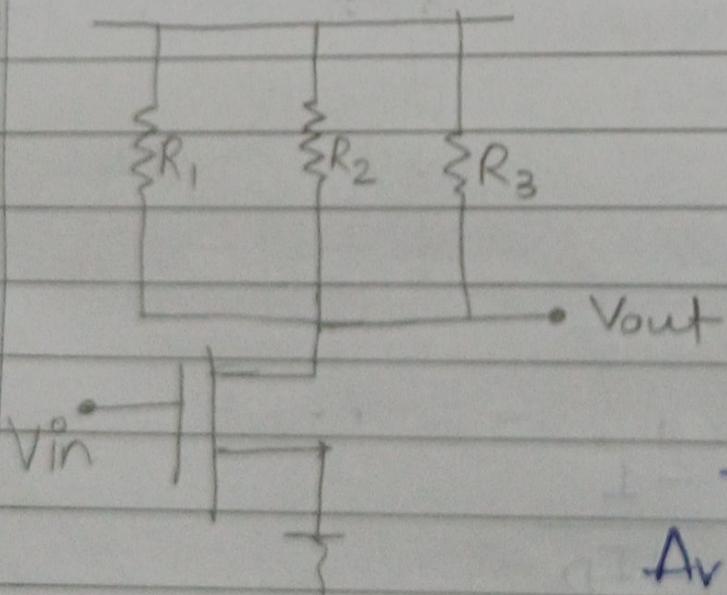
Conclusion:

Z_{out} = Resistance connected to drain

Gain = $-g_m \times$ Resistance connected to drain

= Transconductance of input transistor $\times R$

Q.



find Z_{in}^o , Z_{out} , A_v , and assume $I \neq 0$.

$$Z_{in}^o = \infty$$

$$Z_{out} = R_1 \parallel R_2 \parallel R_3 \parallel r_o$$

$$A_v = -g_m (R_1 \parallel R_2 \parallel R_3 \parallel r_o)$$

Standard values:

For NMOS - $I_{Nl} = 0.1 V^{-1}$

For PMOS - $I_p = 0.2 V^{-1}$

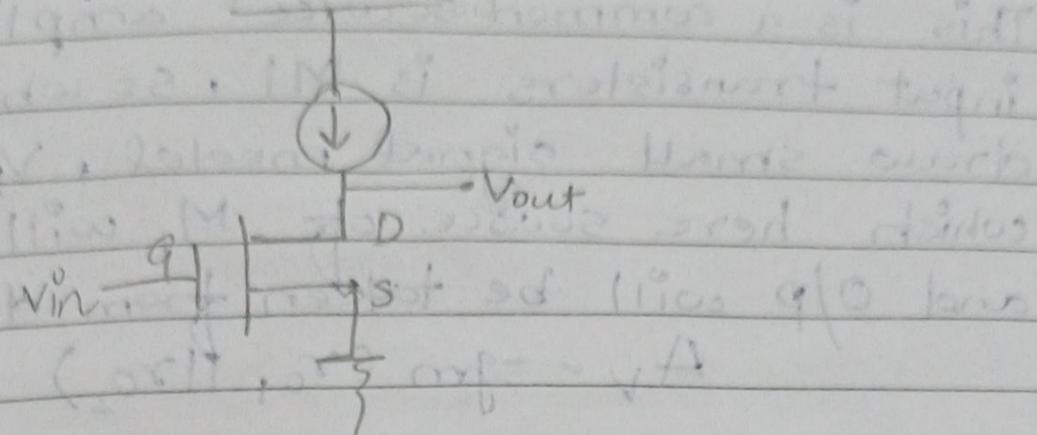
: Intrinsic gain of MOSFET

V_b → Biasing Voltage which is a DC voltage.

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Date :

To find intrinsic gain of MOSFET, replace R_p by a current source.



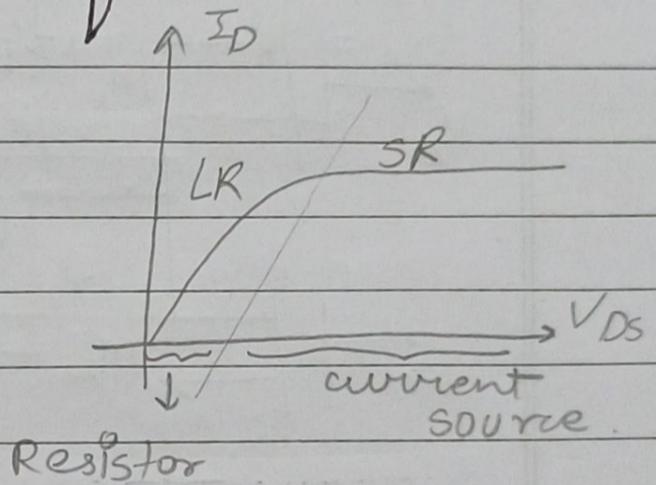
Input characteristics of MOSFET

$$R = \frac{\Delta V}{\Delta I} = \frac{V_o}{I_o}$$

- ∞

$$A_V = -g_m(r_0/1\infty)$$

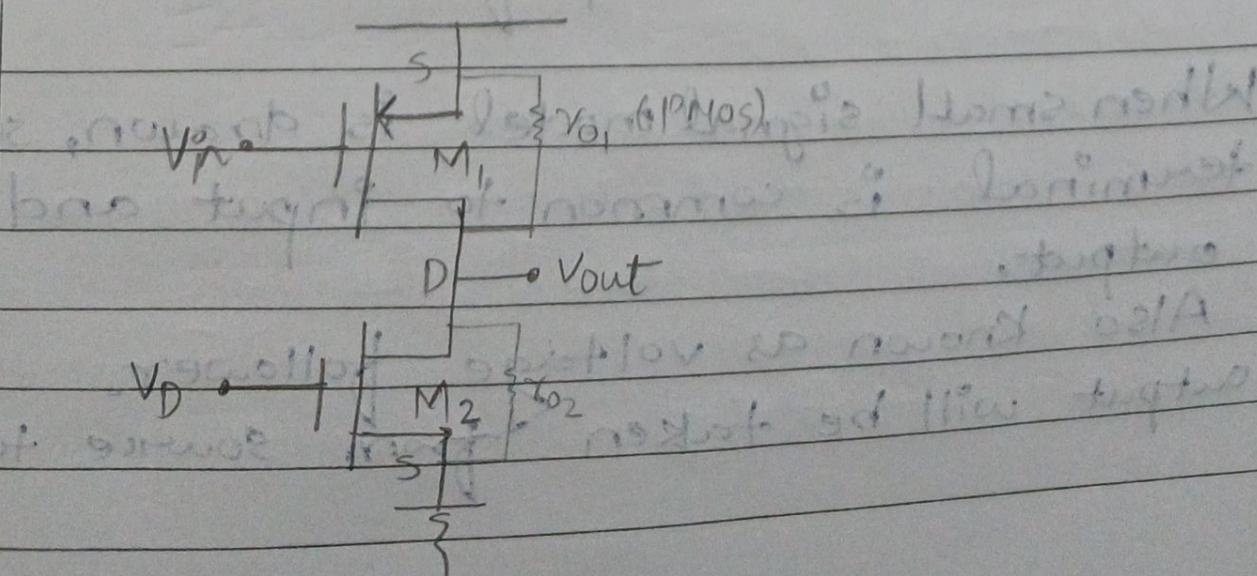
$$A_V = -g m r_0$$



$$g_m = \frac{2ID}{V_{ov}} , \quad r_o = \frac{VA}{ID}$$

$$A_V = \frac{-2VA}{V_{AV}}$$

Q. Find the voltage gain of following configurations.

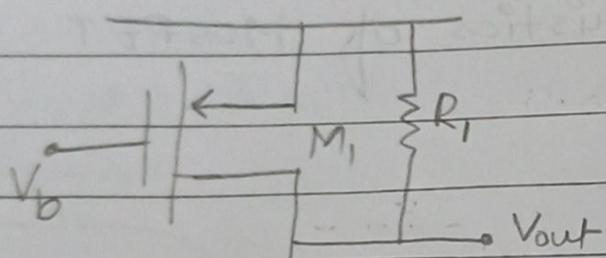


Input transistor = M_1 , (Input is given to one of M_1)

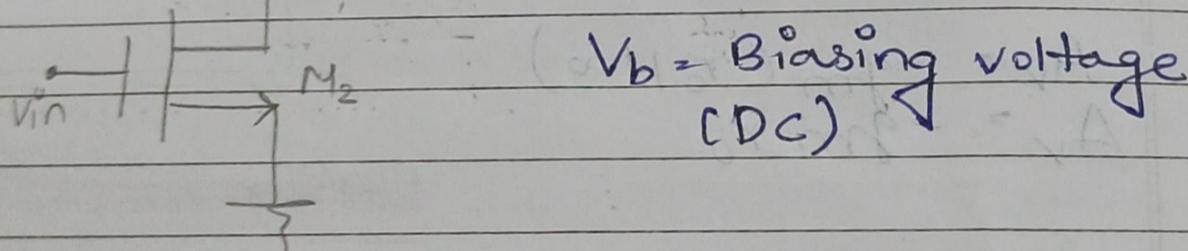
This is a common source amplifier because input transistors is M_1 , so when you draw small signal model, V_D is grounded which here source of M_1 will be grounded and O/P will be taken from drain.

$$A_V = -g_m (r_o + R_o)$$

Q.



Find A_V if
i) $\beta = 0$
ii) $\beta \neq 0$



$$V_b = \text{Biasing voltage (DC)}$$

i) $\beta = 0$

$$A_V = -g_m R_1$$

ii) $\beta \neq 0$

$$A_V = -g_m (r_o + R_1 + r_o)$$

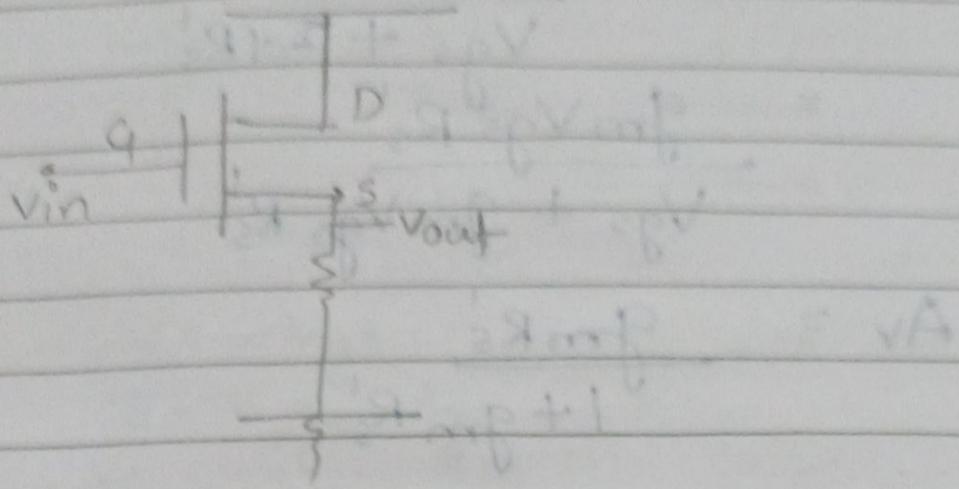
2) Common drain amplifier

→ When small signal model is drawn, source terminal is common to input and output.

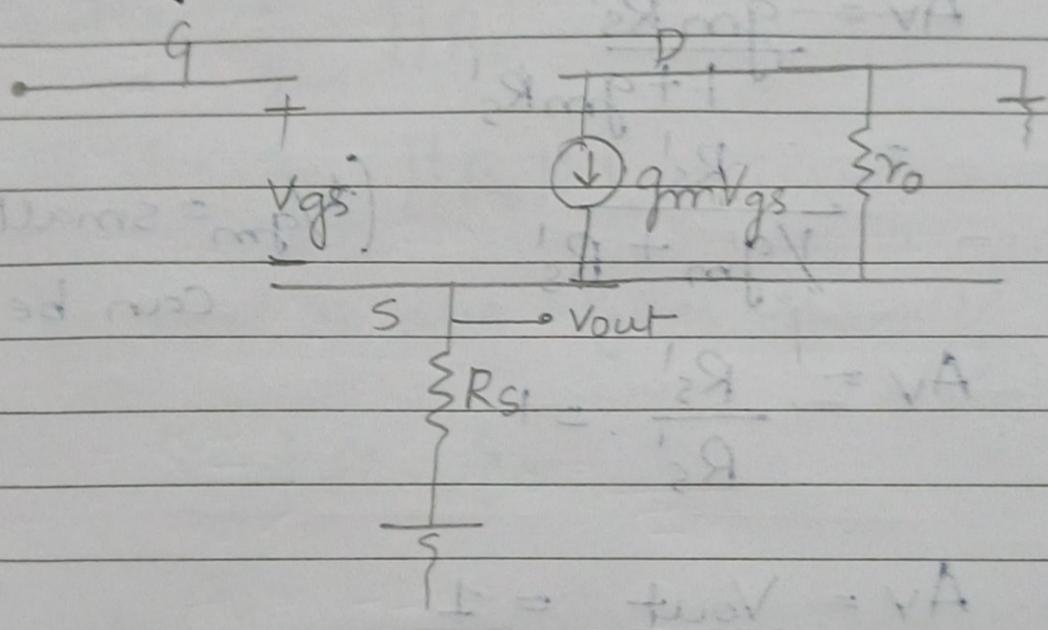
→ Also known as voltage follower.

→ Output will be taken from source terminal.

Input will be given to gate. Load P_s connected to source terminal.



Small signal model.



This is initial circuit so only R_s are in parallel.

$$Z_{in} \rightarrow V_{gs}$$

$$\text{two } \frac{1}{g_m V_{gs}} + \text{trans.}$$

Input impedance $Z_{in} = \infty$

$$\text{Voltage gain } Av = \frac{V_{out}}{V_{in}}$$

4)

$$= \frac{I_d R_s'}{V_{gs} + I_d R_s'}$$

$$= \frac{g_m V_{gs} R_s'}{V_{gs} + g_m V_{gs} R_s'}$$

$$Av = \frac{g_m R_s'}{1 + g_m R_s'}$$

$$R_s' = \text{load resistance} = KV^2$$

$$Av = \frac{g_m R_s'}{1 + g_m R_s'}$$

$$= \frac{R_s'}{Y g_m + R_s'}$$

($1/g_m$ = small quantity
can be neglected)

$$Av = \frac{R_s'}{R_s'} = 1$$

$$Av = \frac{V_{out}}{V_{in}} = 1$$

$V_{out} \approx V_{in}$ (voltage follower.)

NOTE

: To find Z_{out} (there are 2 branches unlike a)

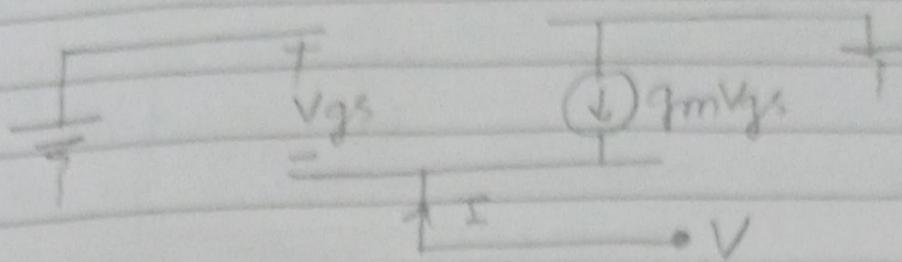
1) Short the V_{in}

2) Remove the load R_s' .

3) We connect a voltage V to the output terminal and then find $\frac{V}{I}$.

(this will give resistance of the top part
in a small-signal model) - pg. I

$$4) Z_{out} = \frac{V}{I} || R_s$$



$$V = -V_{gs}$$

$$I = -g_m V_{gs}$$

$$\frac{V}{I} = \frac{1}{g_m}$$

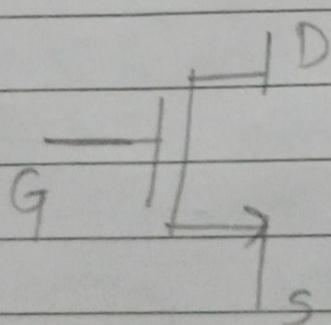
$$Z_{out} = \frac{1}{g_m} || R_s$$

$$Z_{out} = \frac{1}{g_m} || R_s || r_o$$

As R_s and r_o are higher than $\frac{1}{g_m}$.

$$Z_{out} \approx \frac{1}{g_m}$$

NOTE:



looking from source: $R = \frac{1}{g_m}$

looking from gate: $R = \infty$

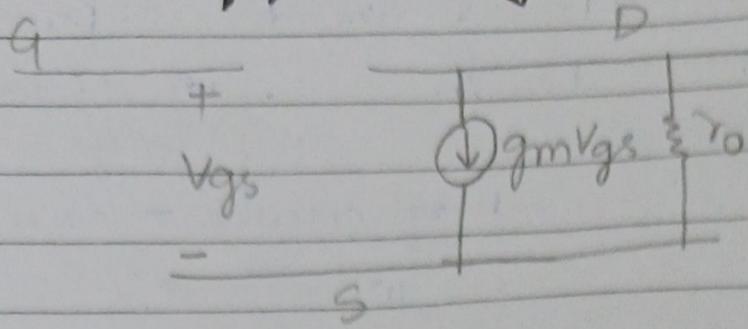
looking from drain: $R = r_o$

: Diode connected load

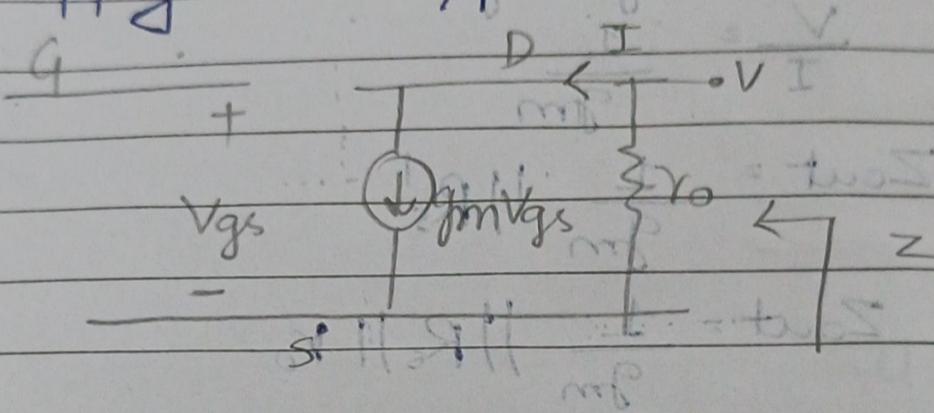
↳ Saturation region

↳ MOSFET behaves as a 2-terminal device, it is called as Diode and offers only resistance (\therefore load)

Resistance offered by diode connected load

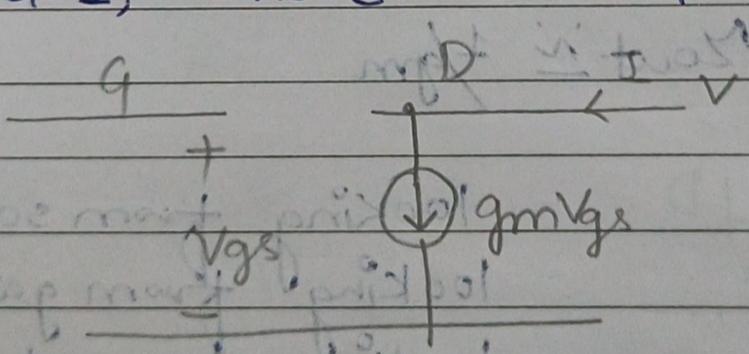


To find the impedance from output side, apply V to o/p side.



$V = V_{gs}$ (input bias or bias $\approx 2A$)

To find I , remove r_o load temporarily.



$$I = g_m V_{gs}$$

$$\frac{V}{I} = \frac{1}{g_m}$$

$$Z = \frac{1}{g_m} || r_o \approx 1/g_m$$

(r_o value = very high)

(load is short circuit due to r_o)

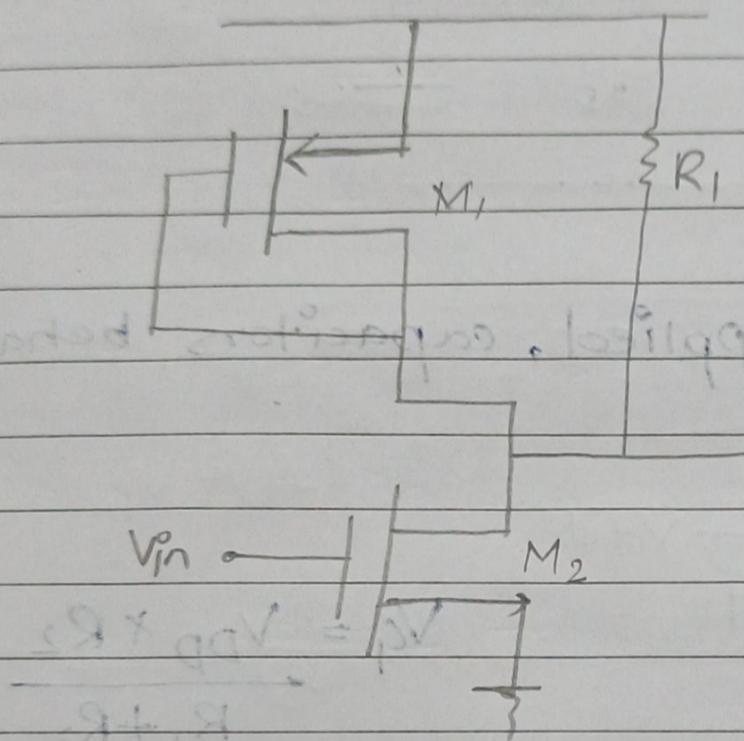
$$Z \approx \frac{1}{g_m}$$

Impedance offered by a diode connected load is very low

In saturation region, Z_{offered} should be ∞ . But in case of diode connected load although it is in SR, it will offer very low impedance. Diode connected load cannot be used as current source because it offers very low Z .

Q find A_V of the following circuit

$$A \neq 0$$



M_2 is the input transistor.

source of M_2 is ~~not~~ grounded, so it is CS amplifier.

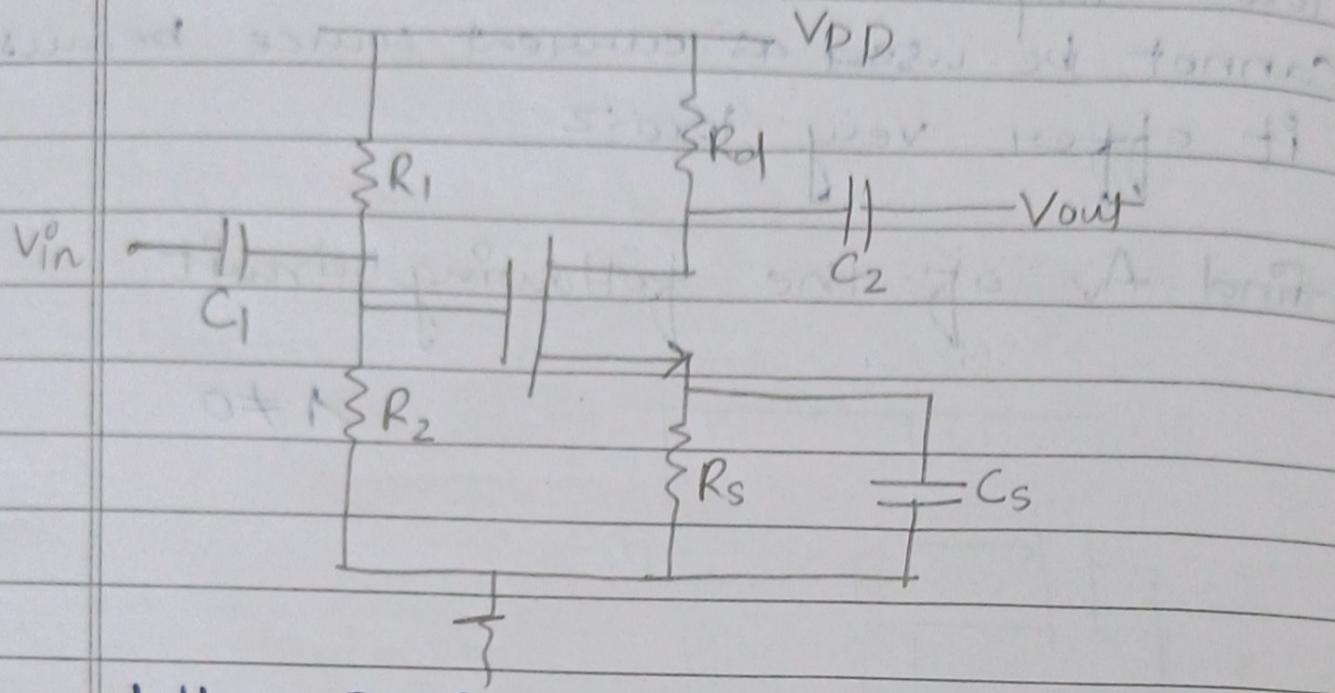
$$A_V = -g_{m_2} (R_1 \parallel r_o \parallel r_{o_2} \parallel \frac{1}{g_{m_1}})$$

Only $\frac{1}{g_{m_1}}$ is lower

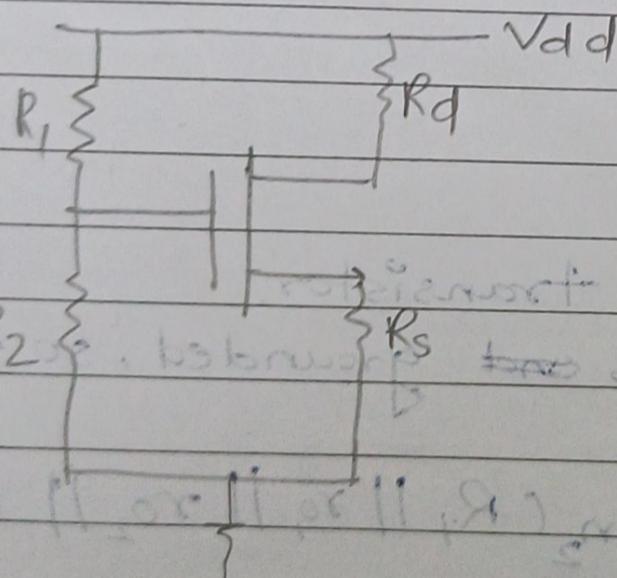
$$A_V = \frac{-g_{m_2}}{g_{m_1}} \cdot \frac{r_o \parallel r_{o_2} \parallel R_1}{r_o \parallel r_{o_2} \parallel R_1}$$

Q. find the gain, Z_{in} , Z_{out} and maximum signal handling capacity of the

transistor if $V_t = 1V$, $k_n (W/L) = 2 \text{ mA/V}_2$
 $V_A = 64.5V$, $V_{DD} = 24V$, $R_i = 8.5M\Omega$,
 $R_2 = 3.5M\Omega$, $R_D = 6K$, $R_s = 2K$



When DC is applied, capacitors behave as open circuit



$$V_G = \frac{V_{DD} \times R_2}{R_1 + R_2}$$

$$= \frac{24 \times 3.5 \times 10^6}{12 \times 10^6}$$

$$V_{GS} = 7V$$

$$R_G = \frac{R_1 R_2}{R_1 + R_2}$$

$$R_G = \frac{8.5 \times 3.5 \times 10^6}{12}$$

$$= 2.47 M\Omega$$

$$I_D = \frac{K_n (\omega_L)}{2} (V_g - V_s - V_t)^2$$

$$I_d = \frac{2}{2} [7 - 2 I_d - 1]^2$$

$$I_d = (6 - 2 I_d)^2$$

$$4 I_d^2 - 25 I_d + 36 = 0$$

$$I_D = 2.25 \text{ mA}$$

$$V_s = 2 I_D \quad (\text{From } I_d R_s)$$

$$V_s = 4.5 \text{ V}$$

$$V_d = V_{DD} - I_D R_D$$

$$= 24 - 2.25(6)$$

$$V_D = 10.5 \text{ V}$$

Small signal parameter:

$$g_m = \sqrt{2 I_D K_n (\omega_L)}$$

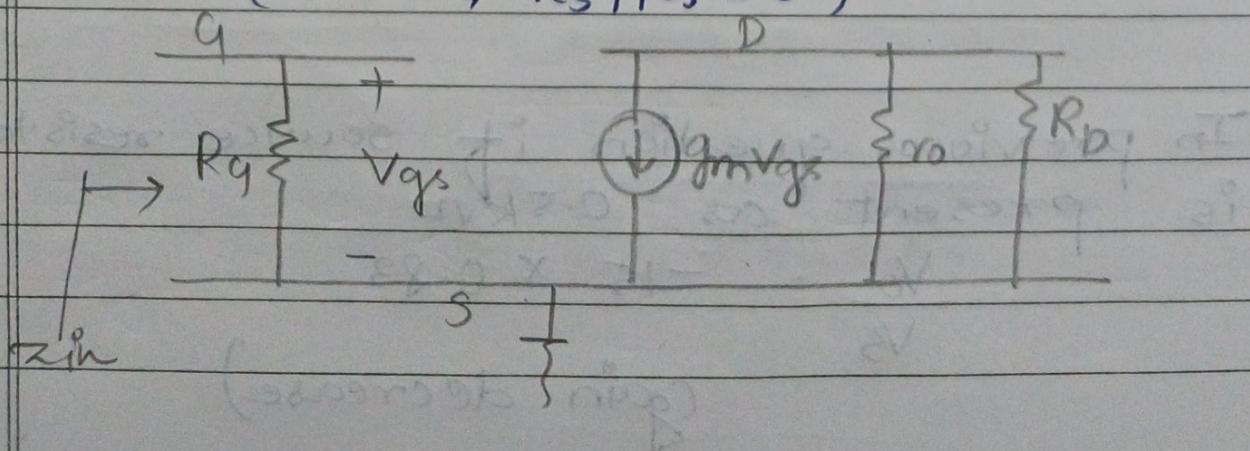
$$g_m = 3 \text{ mA/V}$$

$g_m = \frac{2 I_D}{V_{ov}}$ don't we
until necessary)

$$r_o = \frac{V_A}{I_D} = \frac{67.5}{2.25 \text{ mA}} = 30 \text{ k}\Omega$$

Ac:

Short all DC voltages and open all DC current sources, capacitor shorted
($C_s = 0$, $R_s || C_s = 0$)



$$V_i \rightarrow \text{max input to gate}$$

$$AV = \frac{V_{out}}{V_{in}}$$

$$Z_{in} = R_Q = 2.417 \text{ M}\Omega$$

$$Z_{out} = r_{o11} R_D$$

$$= 8 \text{ k}\Omega$$

$AV = -g_m$ (Resistance connected to drain)
 $= -15$

Max. signal handling capacity

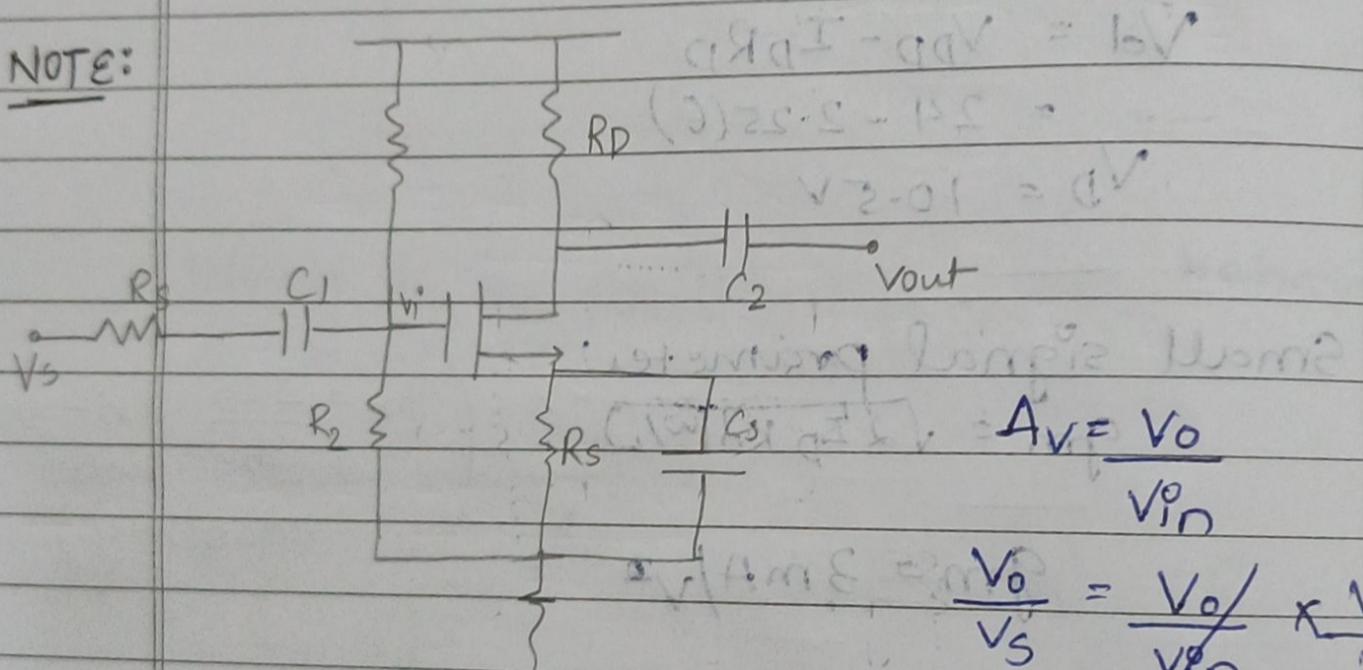
$$V_{DS} \geq V_Q + V_T$$

$$V_D(\text{DC}) + V_{Dc(\text{AC})} \geq V_{Q(\text{DC})} + V_{Q(\text{AC})} - V_T$$

$$10.5 + AV \hat{V}_i \geq 7 + \hat{V}_o - V_T$$

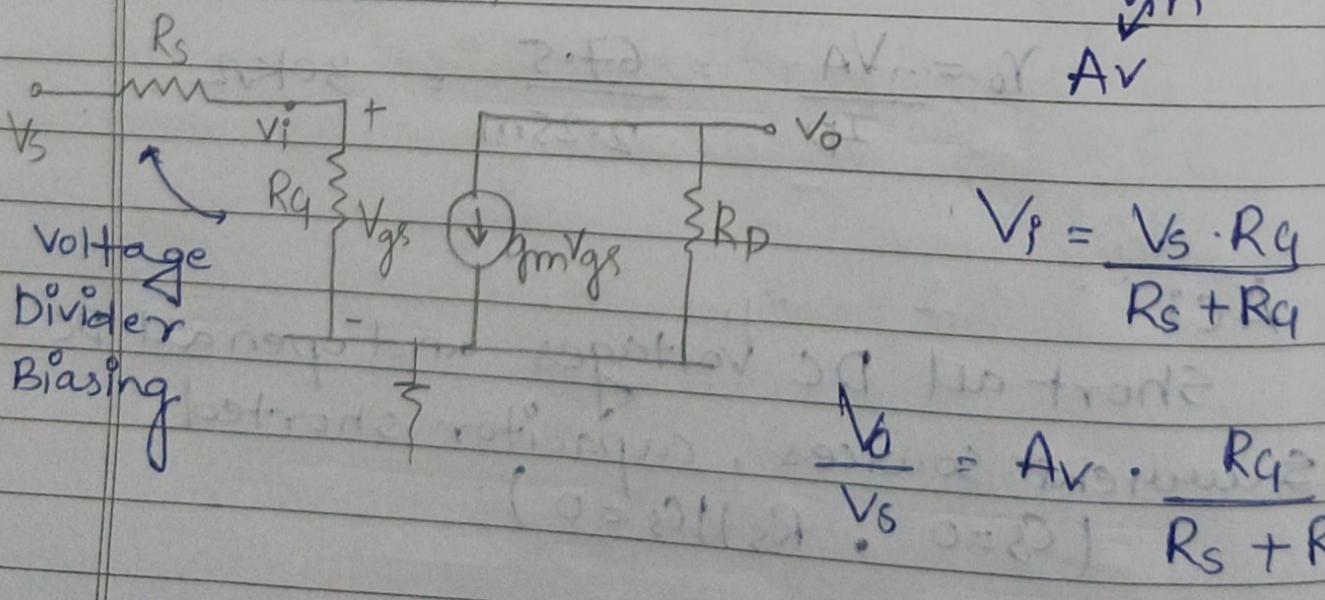
$$\hat{V}_i \leq 0.28 \text{ V}$$

NOTE:



$$AV = \frac{V_o}{V_{in}}$$

$$\frac{V_o}{V_s} = \frac{V_o}{V_{in}} \times \frac{V_{in}}{V_s}$$



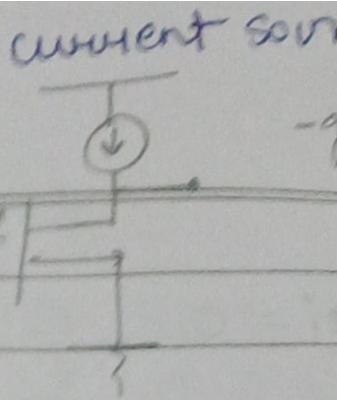
$$V_f = \frac{V_s \cdot R_Q}{R_s + R_Q}$$

$$\frac{V_o}{V_s} = AV \cdot \frac{R_Q}{R_s + R_Q}$$

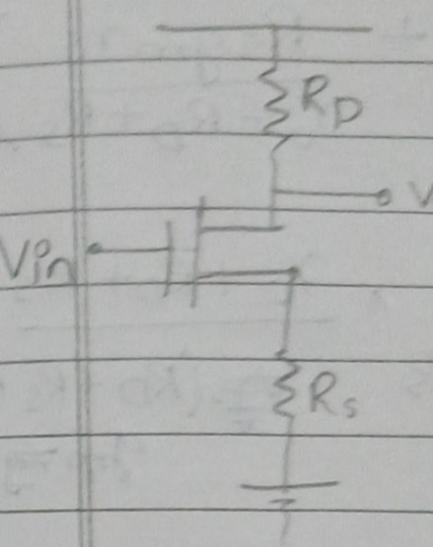
In previous question if source resistance is present as $0.5 \text{ k}\Omega$

$$\frac{V_o}{V_s} = -15 \times 0.83$$

(gain decrease)



: Common s
derivation (Boost th
Proportant L



$$V_{out} = (0 - V_o)$$

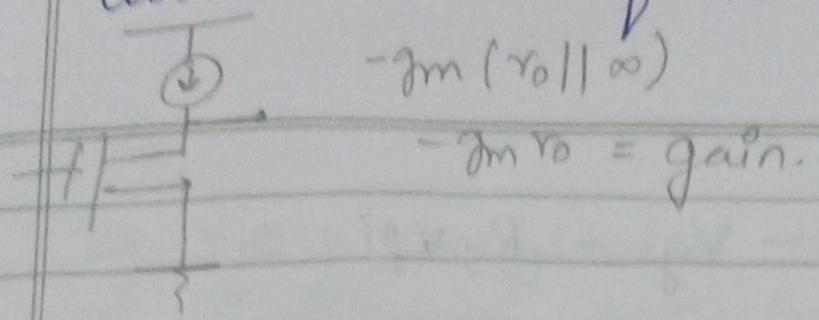
$$j =$$

$$V_{out}$$

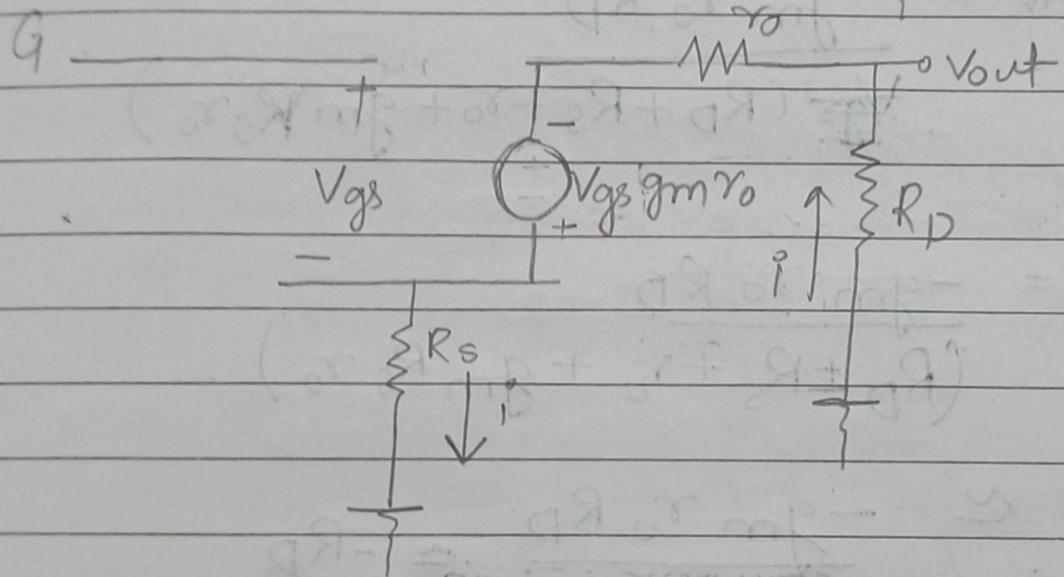
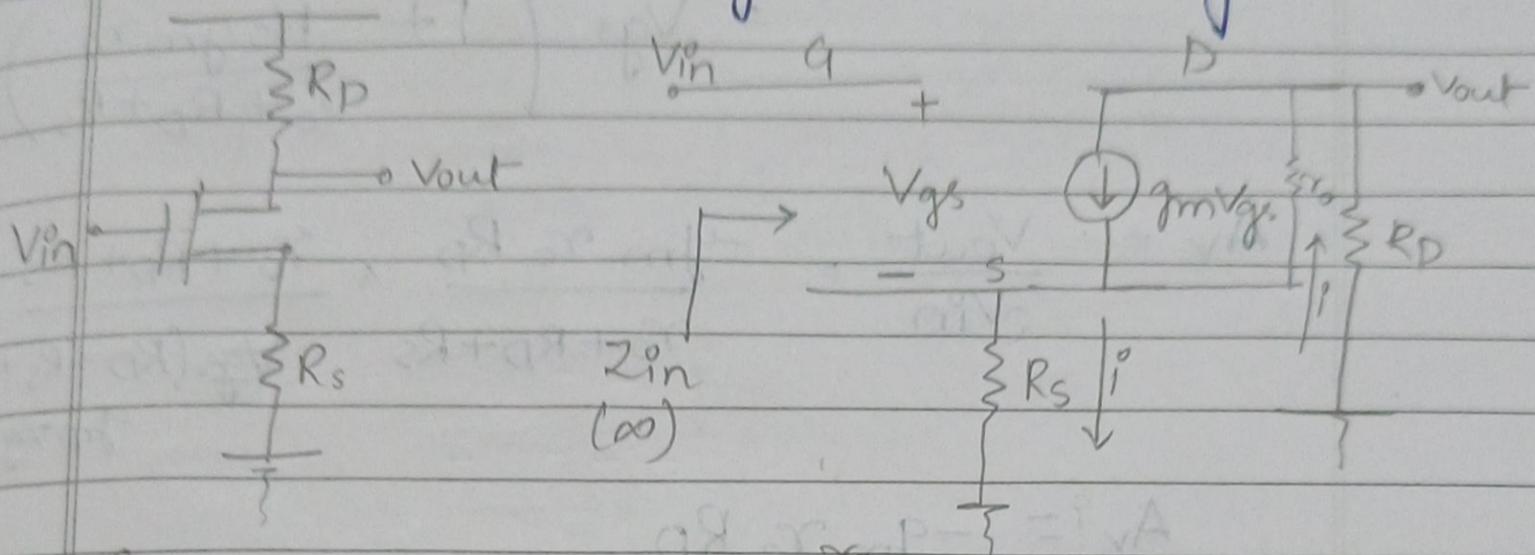
current source = infinite resistance γ_0 = between
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Date:



: Common source with degeneration:
 derivation important (Boost the output impedance)
 cascading becomes easy.



$$V_{out} = -iR_D \quad (i \text{ from ground to } V_{out})$$

$$i = \frac{V_{gs} g_m \gamma_0}{\gamma_0 + R_D + R_S}$$

$$V_{out} = -\frac{V_{gs} g_m \gamma_0 R_D}{\gamma_0 + R_D + R_S}$$

$$\text{Also, } V_{in} - V_{gs} - R_s i = 0$$

$$\begin{aligned} V_{in} &= V_{gs} + R_s i \\ &= V_{gs} + R_s \left(\frac{g_m V_{gs} r_o}{r_o + R_D + R_s} \right) \\ &= V_{gs} \left(1 + \frac{R_s g_m r_o}{r_o + R_D + R_s} \right) \end{aligned}$$

$$A_v = \frac{V_{out}}{V_{in}} = \frac{-g_m r_o R_D}{r_o + R_D + R_s} \times \frac{r_o + R_D + R_s}{V_{gs}(R_D + R_s + r_o + g_m R_s r_o)}$$

$$A_v = \frac{-g_m r_o R_D}{V_{gs}(R_D + R_s + r_o + g_m R_s r_o)}.$$

NOTE: ① $A_v = \frac{-g_m r_o R_D}{(R_D + R_s + r_o + g_m R_s r_o)}$

$$\approx \frac{-g_m r_o R_D}{g_m r_o R_s} \approx \frac{-R_D}{R_s}$$

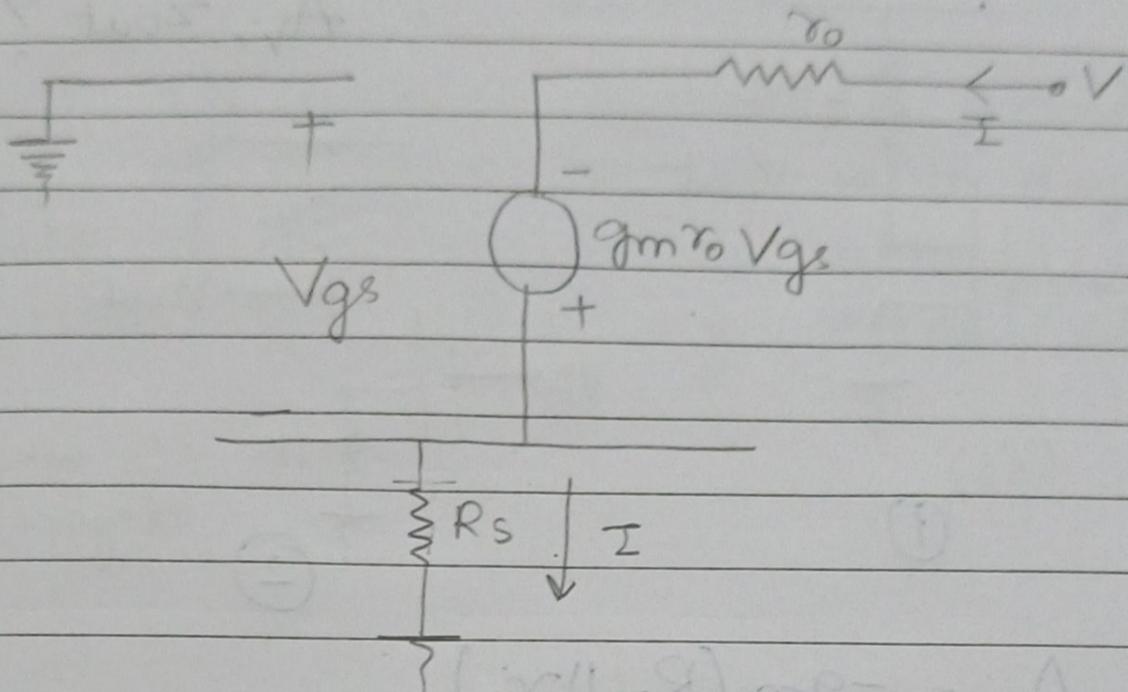
② If $i = 0$:

$$\begin{aligned} A_v &= \frac{-g_m r_o R_D}{R_D + R_s + r_o + g_m r_o R_s} = \frac{-g_m R_D}{R_D + R_s + r_o} + 1 + g_m R_s \\ &= \frac{-g_m R_D}{1 + g_m R_s} = \frac{-R_D}{R_s} \end{aligned}$$

NOTE: R_D II
of
am
Dro

If CLM is neglected then gain is negative of Resistance connected to drain by Resistance connected to source.

Z_{out} :



$$\begin{aligned} V - I r_o + g_m r_o V_{gs} &= 0 \quad | \text{ KVL to } \\ V + g_m r_o V_{gs} &= I(r_o + R_s) \quad | \text{ output loop } \end{aligned}$$

$$\begin{aligned} -V_{gs} - R_s I &= 0 \quad | \text{ KVL to } \\ V_{gs} &= -R_s I \quad | \text{ input loop } \end{aligned}$$

$$V + g_m r_o (-R_s I) = I(r_o + R_s)$$

$$V = I(r_o + R_s + g_m r_o R_s)$$

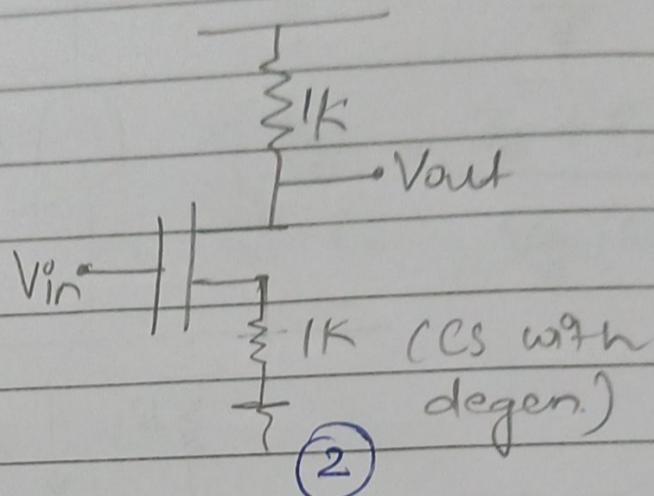
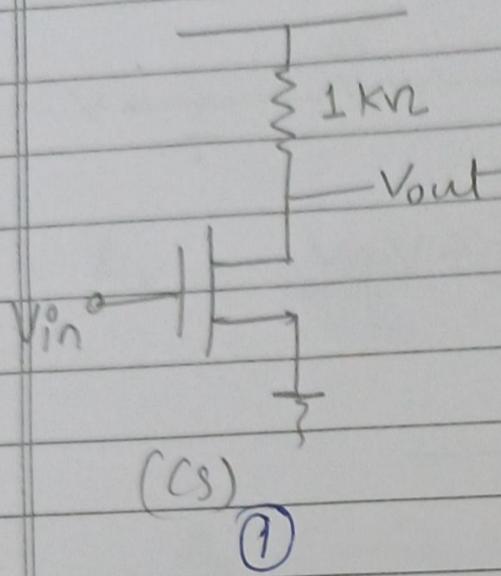
$$\frac{V}{I} = r_o + R_s + g_m r_o R_s$$

NOTE: $R_D || Y_I = R_D$ so there will be no gain of using CS with degeneration so use current source in place of R_D which will provide infinite resistance.

R_D should be a very high value and hence a current source is selected.

Q. $K_n^I = 100 \mu A/V^2$, $w/L = 10$, $I_D = 1mA$
 $r_o = 10K\Omega$

$A_V, z_{out}?$



$$\begin{aligned}
 ① \quad A_V &= -g_m (R_D || r_o) \\
 &= -g_m (1k\Omega || 10k\Omega) \\
 &= -\sqrt{2IDKn^I(\frac{w}{L})} \frac{10k}{11} \\
 &= -\sqrt{2 \times 10^{-3} \times 100 \times 10^{-6} \times 10} \frac{10k}{11} \\
 &= -\sqrt{2 \times 10^{-6}} \cdot 10k \\
 &= -1.41 \times 10^{-3} \cdot 10k \quad R_{out} = R_D || r_o \\
 &= -1.28
 \end{aligned}$$

$$\begin{aligned}
 ② \quad A_V &= \frac{-g_m r_o R_D}{R_D + R_s + r_o + g_m r_o R_s} \\
 &= -\frac{1.41 \times 10^{-3} \times 10 \times 10^3 \times 10^3}{10^3 + 10^3 + 10 \times 10^3 + 1.41 \times 10^{-3} \times 10 \times 10^3 \times 10^3} \\
 &= -\frac{1.41 \times 10^4}{12 \times 10^3 + 1.41 \times 10^4}
 \end{aligned}$$

$$\frac{-1.41 \times 10^4}{26.1 \times 10^3} = -\frac{1.41}{26.1} = -0.54$$

$$R_{out} = r_o + R_s + g_m r_o R_s$$

NOTE: Gain of common source is greater than gain of common source with degen.
R_{out} of common source with degen is greater than R_{out} of common source.